3.3V ECL Differential Receiver

Description

The MC100LVEL16 is a differential receiver. The device is functionally equivalent to the EL16 device, operating from a 3.3 V supply. The LVEL16 exhibits a wider V_{IHCMR} range than its EL16 counterpart. With output transition times and propagation delays comparable to the EL16 the LVEL16 is ideally suited for interfacing with high frequency sources at 3.3 V supplies.

Under open input conditions, the Q input will be pulled down to V_{EE} and the \overline{Q} input will be biased to $V_{CC}/2$. This condition will force the Q output low.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μF capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

Features

- 300 ps Propagation Delay
- High Bandwidth Output Transitions
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.8 V with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = -3.0 V to -3.8 V
- Internal Input Pulldown Resistors on D, Pullup and Pulldown Resistors on D
- Q Output will Default LOW with Inputs Open or at V_{EE}
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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MARKING DIAGRAMS*



SOIC-8 D SUFFIX CASE 751





TSSOP-8 DT SUFFIX CASE 948R





CASE 506AA



A = Assembly Location

= Wafer Lot

Y = Year

W = Work Week

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

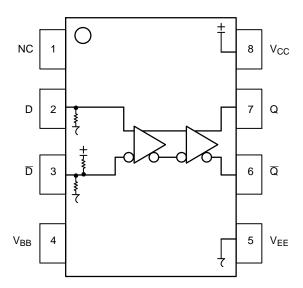


Figure 1. Logic Diagram and Pinout Assignment

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D, D Q, Q V _{BB} V _{CC} V _{EE} NC EP	ECL Data Inputs ECL Data Outputs Reference Voltage Output Positive Supply Negative Supply No Connect (DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. ATTRIBUTES

Characteristic	Value	
Internal Input Pulldown Resistor		75 kΩ
Internal Input Pullup Resistor		75 kΩ
ESD Protection	Human Body Model Machine Model Charged Device Model	> 4 KV > 400 V > 2 kV
Moisture Sensitivity, Indefinite Time out Pb–Free Packages (Note 1)	of Drypack, SOIC-8 TSSOP-8 DFN8	Level 1 Level 3 Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count		79
Meets or Exceeds JEDEC Spec EIA/JE	SD78 IC Latchup Test	

^{1.} Refer to Application Note AND8003/D for additional information.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		8 to 0	V
V _{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-8 to 0	٧
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{c} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 to 0 -6 to 0	V V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
I _{BB}	V _{BB} Sink/Source			± 0.5	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 LFPM 500 LFPM	SO-8 SO-8	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SO-8	41 to 44 ± 5%	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 LFPM 500 LFPM	TSSOP-8 TSSOP-8	185 140	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44 ± 5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W
T _{sol}	Wave Solder Pb Pb-Free	<2 to 3 sec @ 248°C <2 to 3 sec @ 260°C		265 265	°C
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

Table 4. LVPECL DC CHARACTERISTICS $V_{CC} = 3.3 \text{ V}$; $V_{EE} = 0.0 \text{ V}$ (Note 3)

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		17	23		17	23		18	24	mA
V _{OH}	Output HIGH Voltage (Note 4)	2215	2295	2420	2275	2345	2420	2275	2345	2420	mV
V _{OL}	Output LOW Voltage (Note 4)	1470	1605	1745	1490	1595	1680	1490	1595	1680	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2135		2420	2135		2420	2135		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1490		1825	1490		1825	1490		1825	mV
V _{BB}	Output Voltage Reference	1.92		2.04	1.92		2.04	1.92		2.04	V
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 5) Vpp < 500 mV Vpp ≧ 500 mV	1.2 1.5		2.9 2.9	1.1 1.4		2.9 2.9	1.1 1.4		2.9 2.9	V V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current DDD	0.5 -600			0.5 -600			0.5 -600			μ Α μ Α

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
 Outputs are terminated through a 50 Ω resistor to V_{CC} 2 V.
 V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 5. LVNECL DC CHARACTERISTICS $V_{CC} = 0.0 \text{ V}$; $V_{EE} = -3.3 \text{ V}$ (Note 6)

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		17	23		17	23		18	24	mA
V _{OH}	Output HIGH Voltage (Note 7)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV
V _{OL}	Output LOW Voltage (Note 7)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1165		-880	-1165		-880	-1165		-880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	-1810		-1475	-1810		-1475	-1810		-1475	mV
V _{BB}	Output Voltage Reference	-1.38		-1.26	-1.38		-1.26	-1.38		-1.26	V
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 8) Vpp < 500 mV Vpp ≧ 500 mV	-2.1 -1.8		-0.4 -0.4	-2.2 -1.9		-0.4 -0.4	-2.2 -1.9		-0.4 -0.4	V V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current DDD	0.5 -600			0.5 -600			0.5 -600			μ Α μ Α

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
 Outputs are terminated through a 50 Ω resistor to V_{CC} 2 V.
 V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 6. AC CHARACTERISTICS V_{CC} = 3.3 V; V_{EE} = 0.0 V or V_{CC} = 0.0 V; V_{EE} = -3.3 V (Note 9)

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Toggle Frequency		1.75			1.75			1.75		GHz
t _{PLH} t _{PHL}	Propagation Delay to Output Differential Single-Ended	150 100	275 275	400 450	225 175	300 300	375 425	240 190	315 315	390 440	ps
t _{SKEW}	Duty Cycle Skew (Differential) (Note 10)		5	30		5	20		5	20	ps
t _{JITTER}	Random Clock Jitter (RMS)		0.7			0.7			0.7		ps
V_{PP}	Input Swing (Note 11)	150		1000	150		1000	150		1000	mV
t _r t _f	Output Rise/Fall Times Q (20% – 80%)	120	220	320	120	220	320	120	220	320	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 9. V_{EE} can vary ±0.3 V.

^{10.} Duty cycle skew is the difference between a t_{PLH} and t_{PHL} propagation delay through a device.

11. V_{PP(}min) is minimum input swing for which AC parameters guaranteed. The device has a DC gain of ≈40.

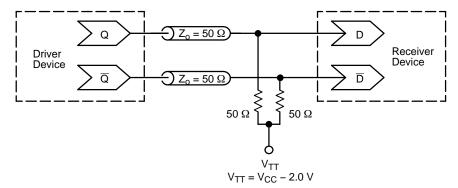


Figure 2. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100LVEL16DG	SO-8 (Pb-Free)	98 Units / Rail
MC100LVEL16DR2G	SO-8 (Pb-Free)	2500 Tape & Reel
MC100LVEL16DTG	TSSOP-8 (Pb-Free)	100 Units / Rail
MC100LVEL16DTR2G	TSSOP-8 (Pb-Free)	2500 Tape & Reel
MC100LVEL16MNR4G	DFN8 (Pb-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

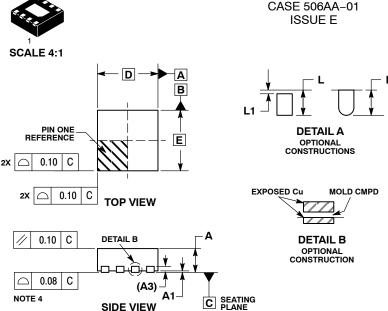
AND8090/D - AC Characteristics of ECL Devices

DETAIL A

е

- D2 →

BOTTOM VIEW



0.10 C

Ф

AB

0.05 C NOTE 3

DFN8 2x2, 0.5P CASE 506AA-01

DATE 22 JAN 2010

NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.80	1.00					
A1	0.00	0.05					
А3	0.20	REF					
b	0.20	0.30					
D	2.00	BSC					
D2	1.10	1.30					
E	2.00 BSC						
E2	0.70	0.90					
е	0.50 BSC						
K	0.30 REF						
L	0.25	0.35					
L1		0.10					

GENERIC MARKING DIAGRAM*

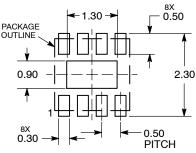


XX = Specific Device Code

= Date Code = Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

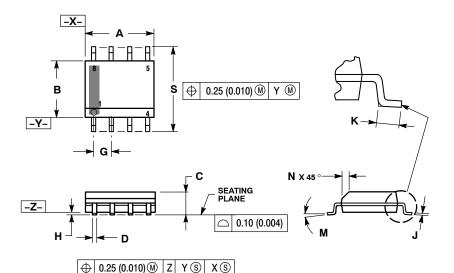
DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Re Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITO	CH	PAGE 1 OF 1		

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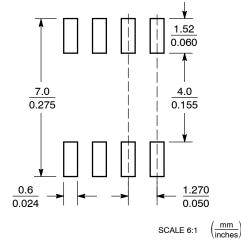
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

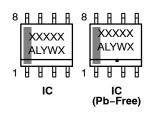
	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.05	0 BSC	
Н	0.10	0.25	0.004	0.010	
7	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

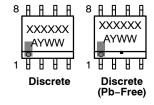
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww

= Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED of the control of	
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

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DATE 16 FEB 2011

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. PINS 2	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7: PIN 1. IMPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2	3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. SOURCE 2. SOURCE
6. BIAS 2 7. INPUT 8. GROUND	5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		
	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 9. COMMON CATHODE/VCC 9. COMMON CATHODE/VCC 1. I/O LINE 1 2. COMMON CATHODE/VCC 1. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 5 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. I/O LINE 5 8. COMMON ANODE/GND 8. SOURCE 9. I/O LINE 5 8. COMMON ANODE/GND 8. VILLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILLIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC 8. VCC 8. VCC 8. VCC 8. VCC 8. SOURCE 2 4. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 7. CATHODE, COMMON 8. N-DRAIN 8. CATHODE, COMMON 8. CATHODE 9IN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 4. GATE 2 5. DRAIN 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 8. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. (/O LINE 1 2. COMMON CATHODE/VCC 1. (/O LINE 3 5. COMMON ANODE/GND 6. (/O LINE 4 7. (/O LINE 5 8. COMMON ANODE/GND 8. LINE 2 OUT 9. COMMON ANODE/GND 8. LINE 1 OUT STYLE 26: PIN 1. GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 28: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMM

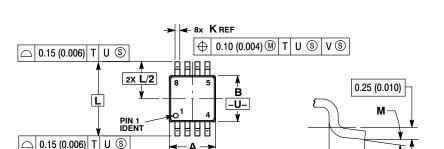
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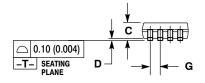
TSSOP 8 CASE 948R-02 ISSUE A

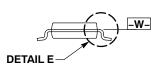
DATE 04/07/2000



-V-

DETAIL E





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 6. DIMENSION A AND B ARE TO BE DETERMINED
- AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
М	0°	6 °	0°	6°

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